

09-24-04

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Express Mail No. EL963273288US
ELM/002 Cont. 4

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Glenn J. Leedy
Application No. : 10/672,961 Confirmation No. : 9439
Filed : September 26, 2003
For : THREE DIMENSIONAL STRUCTURE INTEGRATED
CIRCUIT
Examiner : Not yet assigned
Group Art Unit : 2811

New York, New York 10020
September 23, 2004

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with 37 C.F.R. §§ 1.56 and 1.97,
applicants wish to call the attention of the Examiner to the
following documents:

U.S. Patent Documents

Foster	2,915,722	12/01/59
Farrand	3,202,948	08/24/65
Lesk	3,559,282	02/02/71
Burkhardt	3,560,364	02/02/71
Emmasingel	3,602,982	09/07/71
Medicus	3,615,901	10/26/71
Napoli et al.	3,716,429	02/13/73
Krishna et al.	3,777,227	12/14/73
Kuipers	3,868,565	02/25/75
Yerman	3,922,705	11/25/75
Wanlass	3,997,381	12/14/76
Stein	4,070,230	01/24/78

Greenwood et al.	4,131,985	01/02/79
Hauser, Jr. et al.	4,142,004	02/27/79
Hoeberechts	4,251,909	02/24/81
Kubacki	4,262,631	04/21/81
Shioya et al.	4,394,401	07/19/83
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Schmitz	4,618,763	10/21/86
Christensen	4,663,559	05/05/87
Burns et al.	4,684,436	08/04/87
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Tuckerman	5,274,270	12/28/93
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Leedy	5,354,695	10/11/94
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Wang, et al.	RE 36,623	03/21/00
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"Miniature Electron Microscopes Without Vacuum Pumps, Self-Contained, Microfabricated Devices with Short Working Distances, Enable Operation in Air," *NASA Tech Briefs*, 39-40 (1998).

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Copies of the aforementioned documents, which are listed on the accompanying Form PTO-1449 (submitted in duplicate), except U.S. patents and U.S. patent application publications (1276 OG 55), are enclosed herewith.

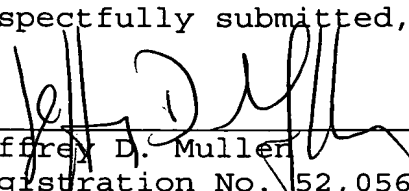
It is respectfully requested that these documents be (1) fully considered by the Patent and Trademark Office during examination of this application; and (2) printed on any patent which may issue on this application. Applicants request that a copy of Form PTO-1449, as considered and initialed by the Examiner, be returned with the next communication.

This Statement is being submitted more than three months from the application filing date but before the mailing date of the first Office Action on the merits.

In accordance with 37 C.F.R. § 1.97(b)(3), submission of this Statement requires no fee. However, if for any reason a fee is due, the Director is hereby authorized to charge payment of any fees required in connection with this Information Disclosure Statement to Deposit Account No. 06-1075. A duplicate copy of this statement is transmitted herewith.

An early and favorable action is respectfully
requested.

Respectfully submitted,



Jeffrey D. Mullen
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Agent for Applicants
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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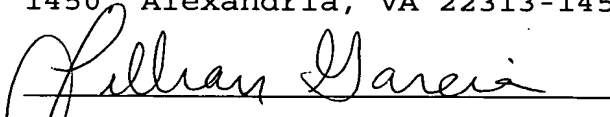
EXPRESS MAIL CERTIFICATION

"Express Mail" Mailing Label No. EL963273288US
Date of Deposit: September 23, 2004

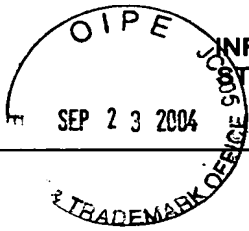
I hereby certify that this certification and the following papers and fees:

1. Information Disclosure Statement (in duplicate);
2. Form PTO-1449 (in duplicate);
3. Copies of forty-one (41) cited references; and
4. Return postcard

are being deposited with the United States Postal Service "EXPRESS MAIL POST OFFICE TO ADDRESSEE" service under 37 C.F.R. § 1.10 on the date indicated above and are addressed to Mail Stop Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.


Name: Lillian Garcia

FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
ELM/002 Cont. 4APPLN. NO.
10/672,961APPLICANTS
Glenn J. LeedyCONF. NO.
9439FILING DATE
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2811INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	2,915,722	12/01/59	Foster	336	115	
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	4,617,160	10/14/86	Belanger et al.	264	40.1	
	4,618,397	10/21/86	Shimizu et al.	156	628	
	4,618,763	10/21/86	Schmitz	250	211R	
	4,663,559	05/05/87	Christensen	313	336	

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	APPLICANTS Glenn J. Leedy	CONF. NO. 9439
	FILING DATE September 26, 2003	GROUP ART UNIT 2811

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		FILING DATE September 26, 2003	GROUP ART UNIT 2811

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